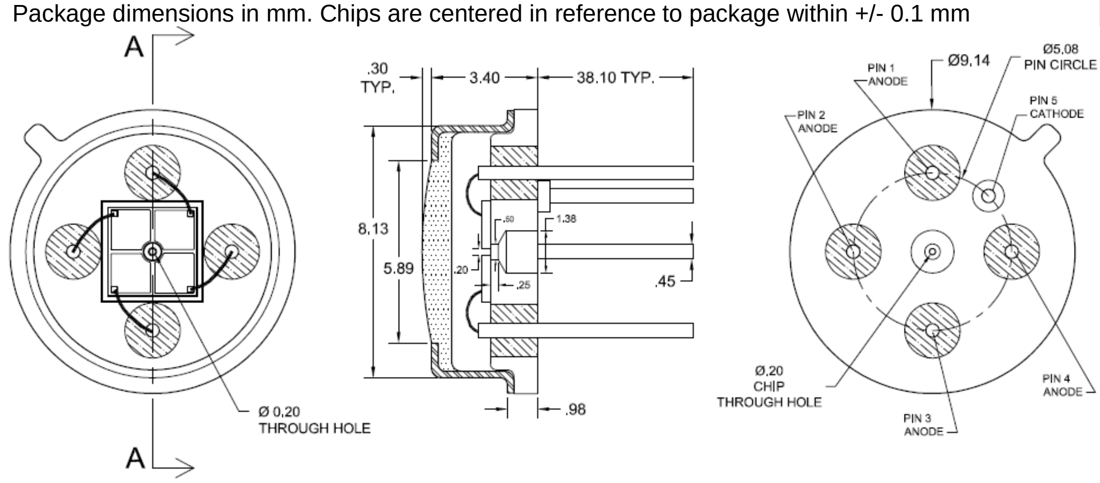
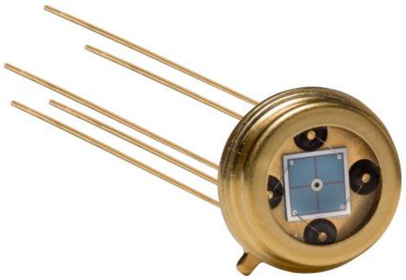
OSI Optoelectronics
An OSI Systems Company

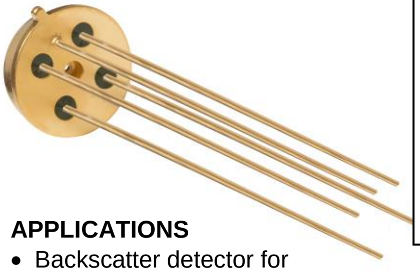
SPOT-4D-0: Annular Quadrant Silicon Photodiode

350nm to 1100nm

Package dimensions in mm. Chips are centered in reference to package within +/- 0.1 mm







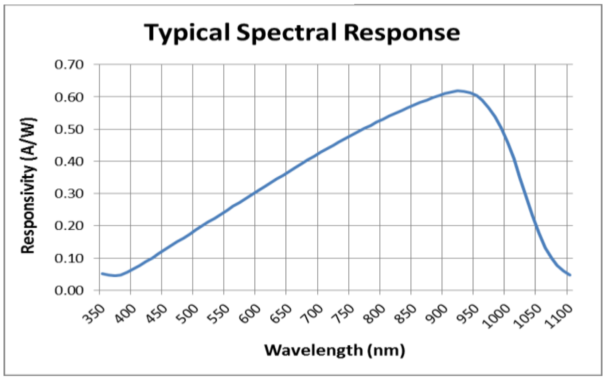
Actual unit may differ

APPLICATIONS

- Backscatter detector for reflectivity measurements

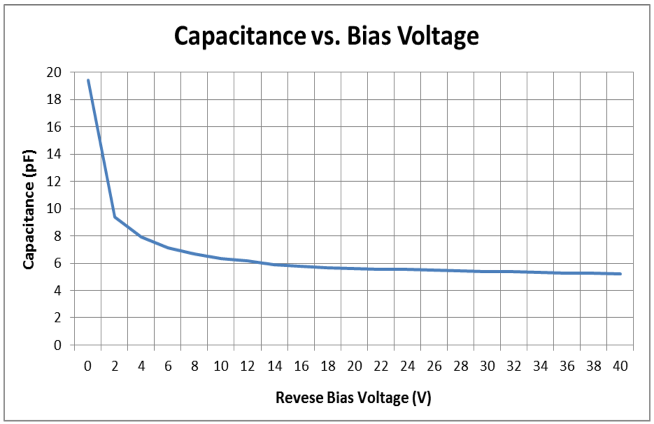
FEATURES

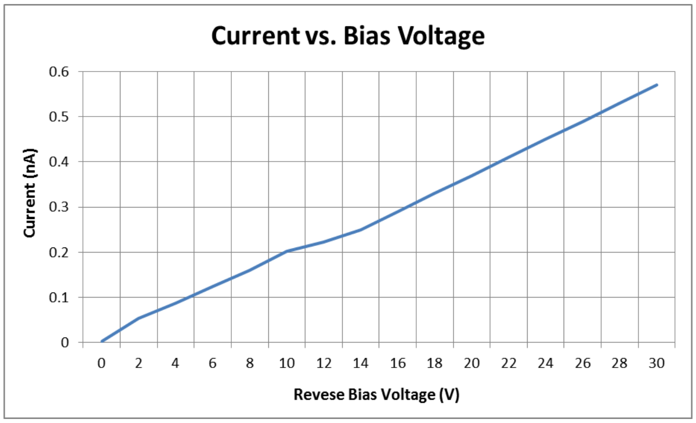
- 350-1100nm Range
- Quadrant Detector
- ϕ200µm laser cut hole on chip
- Annular package design ideal for coupling with LC ferrule


Typical Spectral Response

TYPICAL ELECTRO-OPTICAL CHARACTERISTICS PER ELEMENT @ 23°C

CHARACTERISTIC	CONDITIONS	MIN	TYP	MAX	UNITS
Active Area Per Element			1.3 x 1.3		mm
Element Gap			0.127		mm
Spectral Range		350		1100	nm
Peak Wavelength			980		nm
Responsivity	@ 790 nm		0.52		A/W
Capacitance	@ -10 V		5		pF
Dark Current	@ -10 V		0.1	1	nA
NEP	@ -10 V, 970 nm		8.70E-15		W/?Hz
Reverse Voltage				30	V
Rise Time	@ 780nm, -10V, RL=50 Ohms		6		ns
Operating Temperature		-20		+60	°C
Storage Temperature		-20		+80	°C


Capacitance vs. Bias Voltage


Current vs. Bias Voltage